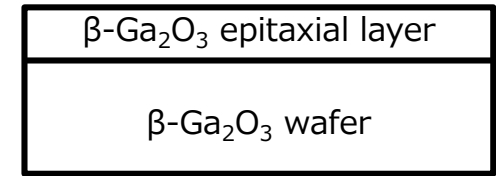


# Standard specifications of MBE $\beta$ -Ga<sub>2</sub>O<sub>3</sub> epitaxial wafers

Epitaxial layer (Growth method: MBE)

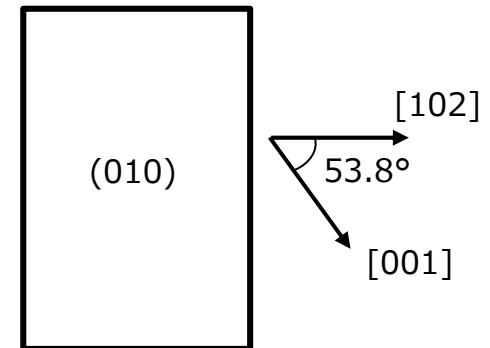
Property	Specification	
Dopant	Si (n-type)	Undoped (semi-insulating)
Doping concentration	Specify a value in the range between $1 \times 10^{17}$ and $2 \times 10^{18} \text{ cm}^{-3}$	-
Thickness	Specify a value in the range between 0.1 and 0.5 $\mu\text{m}$	



Cross section of  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> epitaxial wafers

Wafers

Property	Specification	
Dopant	Sn (n-type)	Fe (semi-insulating)
Doping concentration	$1-9 \times 10^{18} \text{ cm}^{-3}$	-
Resistivity	-	$\geq 10^{10} \Omega\text{cm}$
Orientation	(010)	
Size	10x15 mm <sup>2</sup>	
Thickness	0.5 mm	
XRD FWHM	$\leq 150 \text{ arcsec}$	
Off set angle	$0^\circ \pm 1^\circ$	



Orientation



**Novel Crystal Technology, Inc.**

Remarks

- 1 These products must be used for research and development purposes only.
- 2 The substrates must not be used as a seed crystal.
- 3 The specifications are subject to change without notice.